Controlled and Selective etches for Gate All-Around Device Fabrication

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Supplementary information

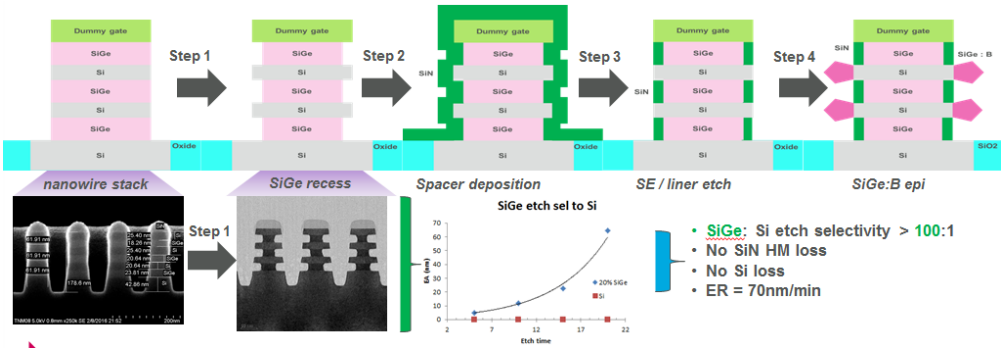

Figure1. Schematic patterning integration flow for a Si NW based GAA device architecture; with gas phase SiGe etch process performance and selectivity data.